

AMENDMENT
U.S. Appln. No. 09/630,777

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film made of an n-type semiconductor and formed on the primer layer, said first n-type semiconductor film as the primer layer (i) having an energy band gap larger than that of said photocatalyst film and (ii) being an oxide semiconductor film consisting essentially of at least one metal oxide selected from the group consisting of niobium oxide, tin oxide, and zirconium oxide.